

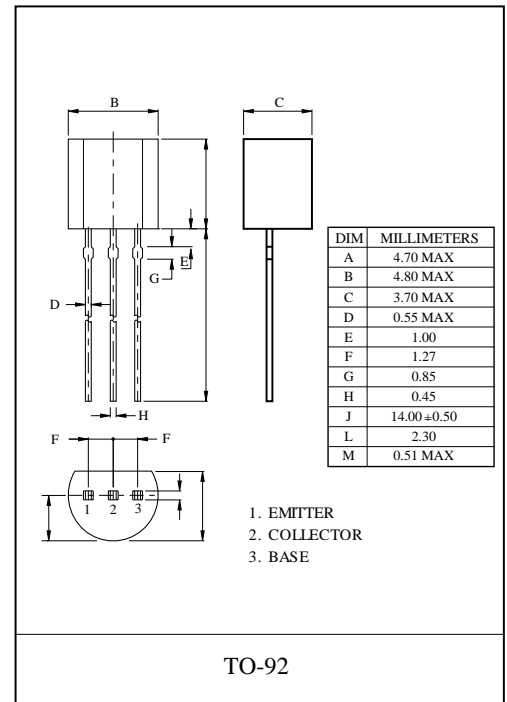
FTC3203 TRANSISTOR (NPN)

FEATURES

- Complementary to FTA1271

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	800	mA
P _C	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



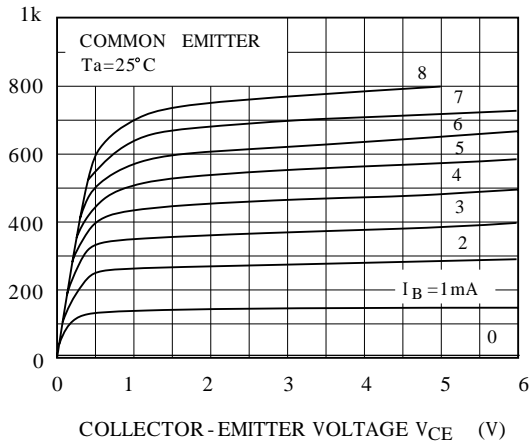
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA, I _B =0	35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 0.1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} = 35V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 25V, I _B =0			0.2	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C = 100mA	100		320	
	h _{FE(2)}	V _{CE} =1V, I _C = 700mA	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500 mA, I _B = 20mA			0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 1V, I _C = 10mA			0.8	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 10mA		120		MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E = 0, f=1MHz		13		pF

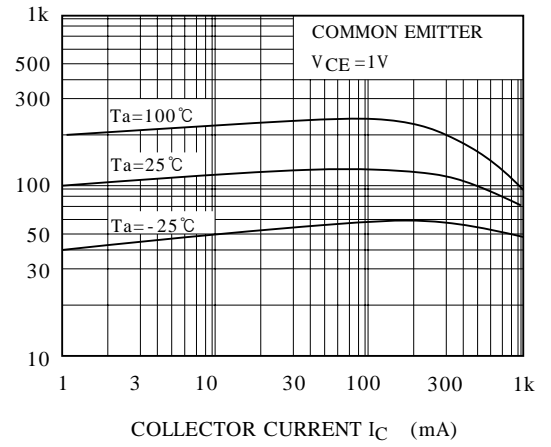
CLASSIFICATION OF h_{FE(1)}

Rank	O	Y
Range	100-200	160-320

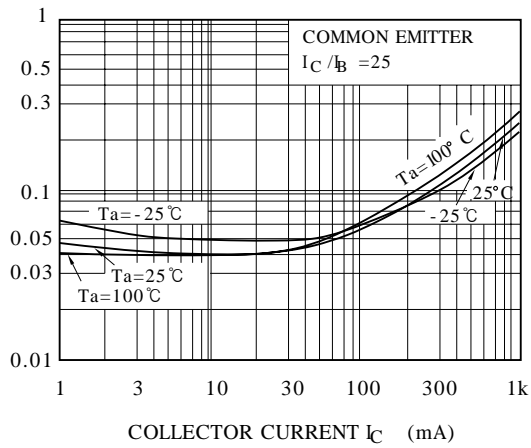
$I_C - V_{CE}$



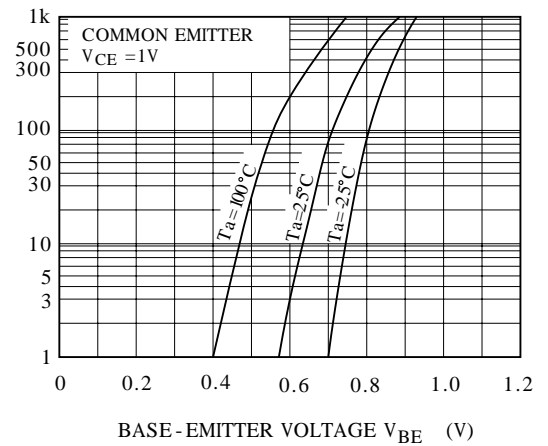
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



$P_c - T_a$

